

isc N-Channel MOSFET Transistor

2SK383

DESCRIPTION

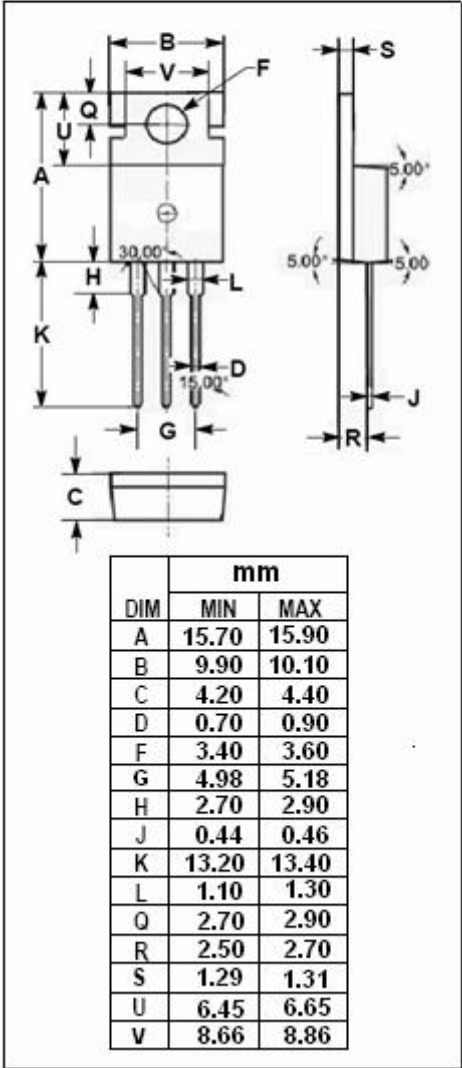
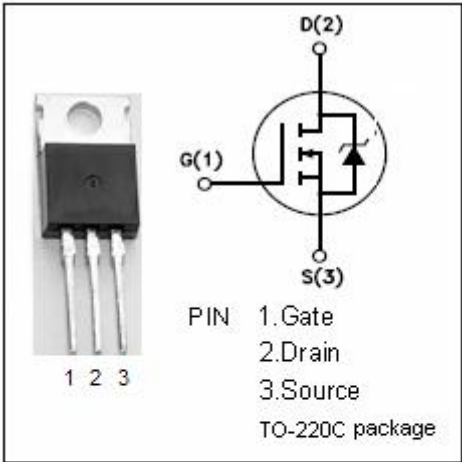
- Drain Current $-I_D=10A@T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}=100V(\text{Min})$
- Fast Switching Speed

APPLICATIONS

- High speed power Switching.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $T_C=25^{\circ}C$	10	A
P_D	Power Dissipation@ $T_C=25^{\circ}C$	50	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc N-Channel MOSFET Transistor**2SK383****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 10mA	100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D = 1mA	2.0		5.0	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} = 15V; I _D = 5A		0.15	0.18	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0			±1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V; V _{GS} = 0			1	mA
V _{SD}	Diode Forward Voltage	I _F = 5A; V _{GS} = 0		0.9		V
t _r	Rise time	V _{GS} =15V; I _D =2A; R _L =15 Ω		50		ns
t _{on}	Turn-on time			60		ns
t _f	Fall time			70		ns
t _{off}	Turn-off time			160		ns